

Title (en)

METHOD FOR WASHING SILICON WAFER

Title (de)

VERFAHREN ZUM WASCHEN EINER SILIZIUMSCHEIBE

Title (fr)

PROCEDE DE LAVAGE D'UNE TRANCHE DE SILICIUM

Publication

EP 0998751 A1 20000510 (EN)

Application

EP 98937071 A 19980721

Priority

- JP 19595997 A 19970722
- US 9815358 W 19980721

Abstract (en)

[origin: WO9905704A1] A method for washing a silicon wafer after an etching treatment includes the steps of: (a) subjecting a silicon wafer after etching to washing and reforming with using a washing-reforming solution, and (b) forming an oxidized film on a surface of the silicon wafer with using an oxidized film forming solution.

IPC 1-7

H01L 21/00

IPC 8 full level

B08B 3/08 (2006.01); **H01L 21/304** (2006.01); **H01L 21/316** (2006.01)

CPC (source: EP KR)

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